

3DA14, 3DA27, 3DA28**NPN Silicon High Frequency High Power Transistor****Features:**

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency, middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications		
			3DA14	3DA27	3DA28
Total Dissipation (Tc≤75°C)	P _{tot}	W	5	50	10
Max. Collector Current	I _{CM}	A	1	5	1
Junction Temperature	T _{jm}	°C	175		
Storage Temperature	T _{stg}	°C	-55~+175		
C-E Breakdown Voltage	V _{(BR)CEO}	V	30~60 (I _c =2mA)	80~250(I _c =5mA)	30~90 (I _c =2mA)
E-B Breakdown Voltage	V _{(BR)EBO}	V	≥5 (I _E =2mA)	≥5 (I _E =5mA)	≥5 (I _E =4mA)
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	1.0	3.0	1.5
			I _c =0.5A, I _B =0.1A	I _c =5A, I _B =1A	I _c =1A, I _B =0.2A
Collector-Base Leakage Current	I _{CBO}	mA	0.5 (V _{CB} =20V)		-
C-E Leakage Current	I _{CEO}	mA	1.0		2.0
			V _{CE} =20V		
Emitter-Base Leakage Current	I _{EBO}	mA	1.0 (V _{EB} =2V)	3.0 (V _{EB} =2V)	-
DC Current Gain	h _{FE}		≥10	≥10	≥10
			V _{CE} =5V, I _c =0.5A	V _{CE} =5V, I _c =1.5A	V _{CE} =5V, I _c =0.75A
Transition frequency	f _T	MHz	≥100	≥5	≥30
			V _{CE} =5V, I _c =0.2A f _o =10 MHz	V _{CE} =5V, I _c =0.5A f _o =10 MHz	V _{CE} =5V, I _c =0.2A f _o =10 MHz

Outline and Dimensions: